ON Semiconductor®

Final Product/Process Change Notification

Document #:FPCN22966XI
Issue Date:27 Jul 2021

Title of Change:	Qualification of FS3 Trench IGBT 12inch Technology at Global Foundries in New York, US and 8inch FRD technology at ON semi CZ4 Manufacturing site in Roznov, Czech for Wafer Fab Capacity Expansion
Proposed First Ship date:	06 Nov 2021 or earlier if approved by customer
Contact Information:	Contact your local ON Semiconductor Sales Office or Bokyun.Seo@onsemi.com
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office or <PCN.samples@onsemi.com>. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Byeongyeop.Lee@onsemi.com
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact PCN.Support@onsemi.com
Marking of Parts/ Traceability of Change:	No change for the marking of parts & Product date code
Change Category:	Wafer Fab Change
Change Sub-Category(s):	Manufacturing Site Addition

Sites Affected:

ON Semiconductor Sites	**External Foundry/Subcon Sites**
ON Semiconductor Aizu, Japan	Global Foundries East Fishkill, New York, United States
ON Semiconductor Bucheon, Korea	
ON Semiconductor Roznov, Czech Republic	

Description and Purpose:

This is a Final Change Notification (FPCN) to customers announcing the qualification of additional wafer fabrication facility for FS3 TIGBT technology at Global Foundries in New York, US & FRD technology at ON semi CZ4 Manufacturing site in Roznov, Czech.

Qualification tests are designed to show that the reliability of the affected devices will continue to meet or exceed ON Semiconductor standards, with no form, fit or functions alterations.

	Before Change Description	**After Change Description**
Wafer FAB site	ON Semiconductor Bucheon, Korea ON Semiconductor Aizu, Japan	ON Semiconductor Bucheon, Korea ON Semiconductor Aizu, Japan ON Semiconductor Roznov, Czech Republic Global Foundries East Fishkill, New York, United States

There is no product marking change as a result of this change.

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Reliability Data Summary:

QV DEVICE NAME: FGH75T65SHD-F155, FGH75T65SHDT-F155, FGH60T65SHD-F155, FGY160T65SPD-F085
RMS: U78532, U78534, U78535, U78536, U76790, U74188, U74191, U72040
PACKAGE: TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=175°C, 100_% max rated V	1008 hrs	0/240
HTGB	JESD22-A108	Ta=175°C, 100_% max Vge	1008 hrs	0/240
HTSL	JESD22-A103	Ta=175°C, No bias	1008 hrs	0/240
TC	JESD22-A104	Ta= -55°C to + 150_°C	1000 cyc	0/240
HAST	JESD22-A110	130°C, 85% RH, 18.8psia, bias	96 hrs	0/240
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/240
IOL	ML-STD-750	Ta=25°C, delta Tj=100°C On/Off = 5min	3000 cyc	0/240

Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: *Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the* ***PCN Customized Portal****.*

Part Number	Qualification Vehicle
FGA40T65SHDF	FGH75T65SHD-F155
FGH40T65SHDF-F155	FGH75T65SHD-F155
FGA40T65SHD	FGH75T65SHD-F155
FGH40T65SHD-F155	FGH75T65SHD-F155
FGH75T65SHDT-F155	FGH75T65SHDT-F155
FGH75T65SHDTL4	FGH75T65SHD-F155
FGH75T65SHD-F155	FGH75T65SHD-F155